



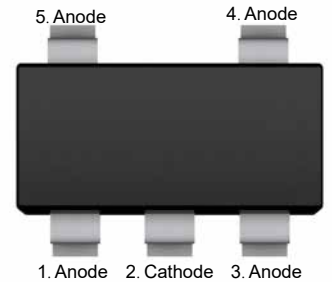
# MMBN187SE

## Silicon Epitaxial Planar Switching Diode

**Features:**

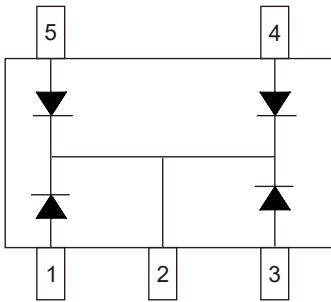
- High Speed switching

**Package:** GCH187-5



**Marking Code:** N187

**Electrical Diagram:**



**Maximum Ratings (at T<sub>J</sub> = 25°C):**

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V <sub>RRM</sub>	80	V
Reverse Voltage	V <sub>R</sub>	80	V
Average Rectified Forward Current	I <sub>F(AV)</sub>	100	mA
Non-Repetitive Peak Forward Surge Current	I <sub>FSM</sub>	1 4	A
		at t = 1s	
		at t = 1μs	
Maximum Power Dissipation	P <sub>D</sub>	350	mW
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C

**Forward Characteristics (at T<sub>J</sub> = 25°C):**

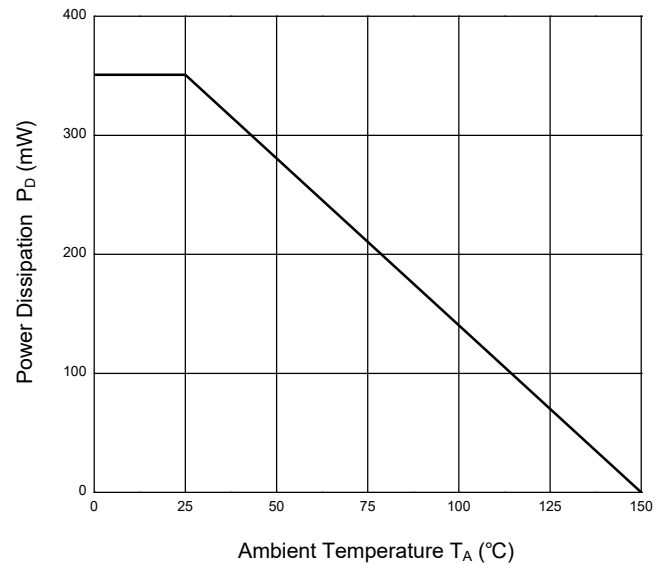
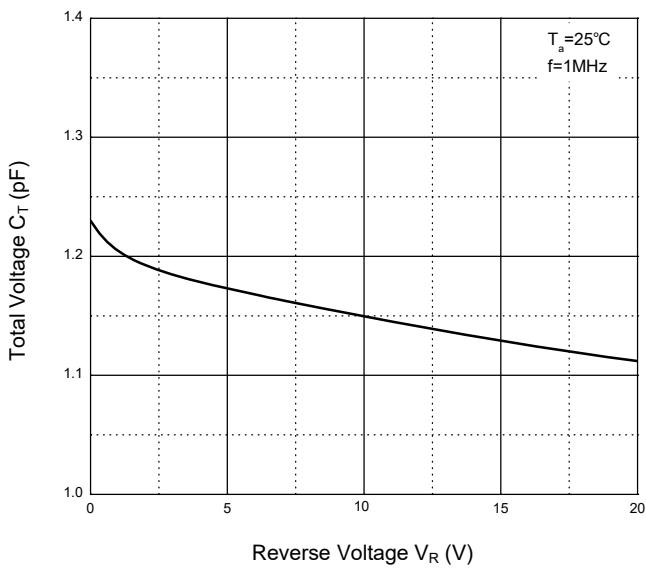
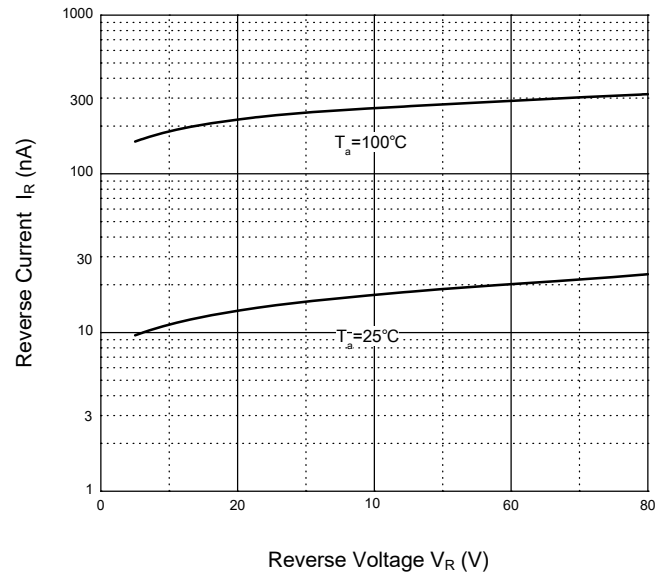
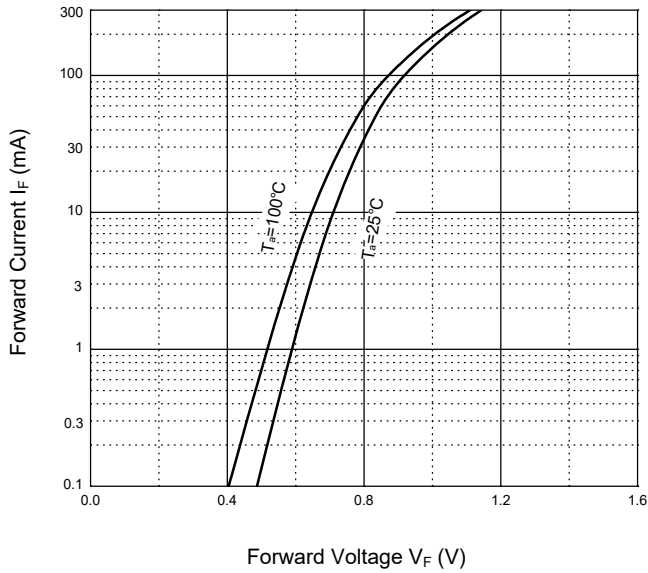
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage	V <sub>F</sub>	--	0.7	V
at I <sub>F</sub> = 5 mA		--		
at I <sub>F</sub> = 10 mA		--	0.85	
Reverse Breakdown Voltage at I <sub>R</sub> = 100 μA	V <sub>(BR)R</sub>	80	--	
Reverse Current at V <sub>R</sub> = 80 V	I <sub>R</sub>	--	1	μA
Typical Junction Capacitance	C <sub>j</sub>	--	3	pF
at V <sub>R</sub> = 0 V, f = 1 MHz				
Maximum Reverse Recovery Time	T <sub>rr</sub>	--	4	nS
at I <sub>F</sub> = I <sub>R</sub> = 10mA, I <sub>rr</sub> = 0.1×I <sub>R</sub>				



# MMBN187SE<sup>†</sup>

## Silicon Epitaxial Planar Switching Diode

### Typical Characteristic Curves





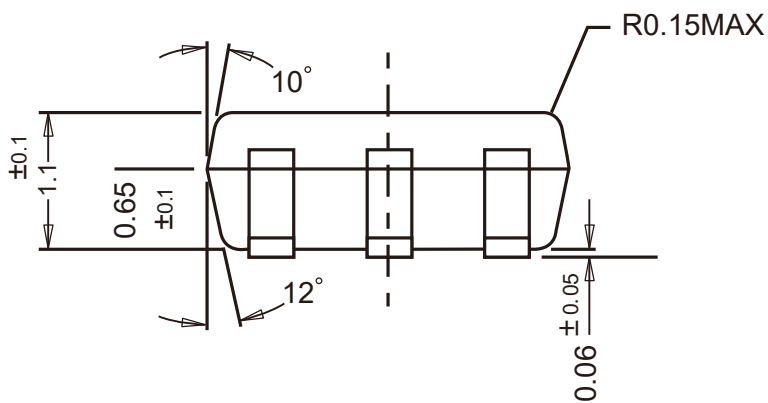
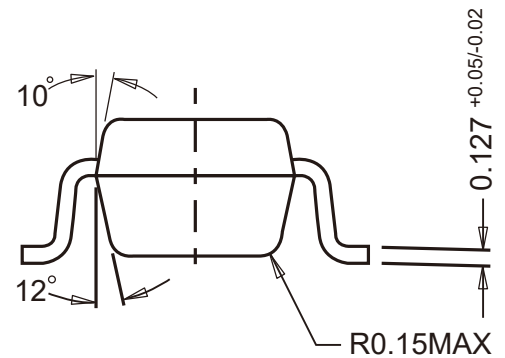
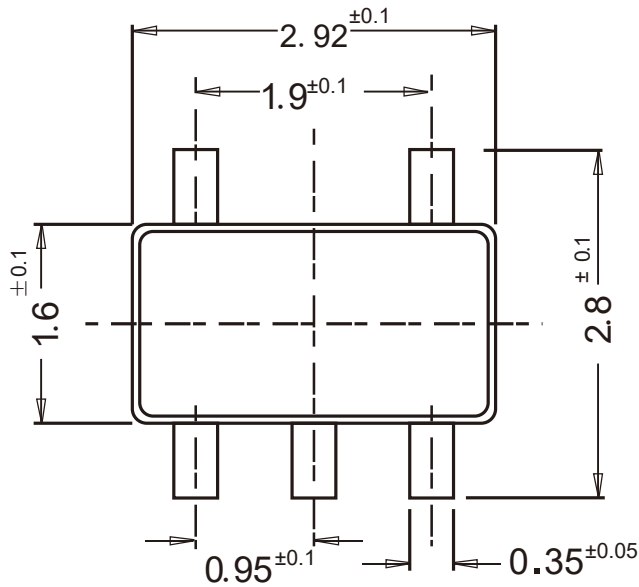
# MMBN187SE<sup>†</sup>

## Silicon Epitaxial Planar Switching Diode

### Package Outline

SOT-23-5

Dimensions in mm



### Ordering Information

Device	Package	Shipping
MMBN187SE	SOT-23-5	3,000PCS/Reel&7inches

单击下面可查看定价，库存，交付和生命周期等信息

[>>PJSEMI\(平晶微\)](#)